# International Conference on Frontiers of Characterization and Metrology for Nanoelectronics 2017

Monterey, California, USA
21-23 March 2017

**Editors:**

**E. M. Secula** **D. G. Seiler**

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# Monday, March 20

## Reception and Registration

**5:30 PM – 8:30 PM**

Ferrante's Bay View Room, 10th Floor, Monterey Marriott

# Tuesday, March 21

## Registration and Breakfast

**7:30 AM – 8:45 AM**

## Conference Opening

**9:00 AM – 9:15 AM**

Welcome and Introduction

*David Seiler, NIST, Conference Chair*

## Keynote Talks

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[2]Sandia National Laboratories, Albuquerque, NM
[3]Materials Science and Engineering Program, Univ. of CA San Diego, La Jolla, CA
[4]Dept of NanoEngineering, Univ. of CA San Diego, La Jolla, CA

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[1]Univ. Grenoble Alpes \ CEA, LETI, MINATEC Campus, Grenoble, France
[2]Univ. Grenoble Alpes \ CNRS, LTM, Grenoble, France
[3]IBM Research, Albany, NY
[4]Univ. Grenoble Alpes, INES, F-73375 Le Bourget du Lac, France

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[1]Imec, Leuven, Belgium
[2]Mat. & Struct. Analysis, Thermo Fisher Scientific, Czech Republic
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[1]Department of Micro- and Nanotechnology, Technical University of Denmark, Lyngby, Denmark
[2]IMEC, Leuven, Belgium
[3]Instituut voor Kern- en Stralingsfysika, Leuven, Belgium
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[1]JILA and Department of Physics, University of Colorado, Boulder, CO
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[1]JILA, University of Colorado, Boulder, CO
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[1]CNSE, SUNY Polytechnic Institute, Albany, NY
[2]TEL Technology Center, America, LLC, Albany, NY
[3]Cornell High Energy Synchrotron Source, Ithaca, NY
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[1]Nanoelectronics Research Institute, National Institute of Advanced Industrial Science and Technology (AIST) West 7A, 16-1 Onogawa, Tsukuba, Ibaraki 305-8569 Japan
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[2]CEA-LETI/ESRF, Grenoble, France
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[1]STMicroelectronics, Crolles, France
[2]Univ. Grenoble Alpes, Grenoble, France
[3]CNRS, LTM, MINATEC Campus, Grenoble, France
[4]Synchrotron SOLEIL, Saint Aubin, Gif-sur-Yvette, France
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[2]Georgia Institute of Technology, Atlanta, GA
[3]University of Califormia, Los Angeles, CA

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[1]Advantest America, Inc., San Jose, CA
[2]Advantest Corporation, Matsubara, Kamiayashi, Aoba-ku, Sendai Japan

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[1]CNSE, SUNY Polytechnic Institute, Albany, NY
[2]Materials Science and Engineering, University of Texas at Dallas, Richardson, TX

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[1]Imec, Leuven, Belgium
[2]Bruker Semiconductor Division, Santa Barbara, CA
[3]Bruker Semiconductor Division, Durham, UK
[4]KU Leuven, Dept. of Physics and Astronomy, Leuven, Belgium

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[1]SK hynix, Inc., Icheon-si, Gyeonggi-do, Korea
[2]Korea Advanced Institute of Science and Technology, Daejeon, Korea

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[1]Department of Electrical and Computer Engineering, University of Toronto, Toronto M5S 3G4, Canada
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[1]Carl Zeiss Microscopy, LLC, Ion Microscopy Innovation Center, Peabody, MA
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[1]Department of Physics, New Mexico State University, Las Cruces, NM
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[3]Dept of NanoEngineering, Univ. of CA San Diego, La Jolla, CA

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